

**Remarks**

1. Amendment of the specification:

5       The main feature of the present invention is forming  
a thin film transistor with two dielectric layers  
thereon. Some typos and improper descriptions are  
corrected in the amended specification. No new matter  
is introduced in the above-mentioned amendment.  
10   Allowance for making the above-mentioned amendment is  
politely requested.

2. Amendment of claims 1 and 4:

15       Claim 4 is combined to claim 1 and therefore  
cancelled. No new matter is introduced in the  
above-mentioned amendment. Allowance for making the  
above-mentioned amendment is politely requested.

20   3. Amendment of claims 1, 2, 7, 8, 11, and 12:

Claims 1, 2, 7, 8, 11, and 12 are amended to be  
identical with the amended descriptions in the  
specification. No new matter is introduced in the  
above-mentioned amendment. Allowance for making the  
25   above-mentioned amendment is politely requested.

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Sincerely yours,

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